



IXFN110N85X Information

www.heisener.com

For Reference Only

Part Number IXFN110N85X

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description 850V/110A ULT JUNCT X-CLASS HIPE

Package SOT-227-4, miniBLOC

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IXFN110N85X Specifications

Manufacturer Part NumberIXFN110N85XManufacturerIXYSCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackageSOT-227-4, miniBLOCSeriesHiPerFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)850VCurrent - Continuous Drain (Id) @ 25°C110A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5.5V @ 8mAGate Charge (Qg) (Max) @ Vgs425nC @ 10VInput Capacitance (Ciss) (Max) @ Vds17000pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1170W (Tc)Rds On (Max) @ Id, Vgs33 mOhm @ 55A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227BPackage / CaseSOT-227-4, miniBLOC		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single SOT-227-4, miniBLOC Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Parin to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Liput Capacitance (Ciss) (Max) @ Vds PET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Askage / Case Package / Case Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single SOT-227-4, miniBLOC	Manufacturer Part Number	IXFN110N85X
Package SOT-227-4, miniBLOC Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 850V Current - Continuous Drain (Id) @ 25°C 110A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 425nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 17000pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1170W (Tc) Rds On (Max) @ Id, Vgs 33 mOhm @ 55A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227B Package / Case SOT-227-4, miniBLOC	Manufacturer	IXYS
PackageSOT-227-4, miniBLOCSeriesHiPerFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)850VCurrent - Continuous Drain (Id) @ 25°C110A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5.5V @ 8mAGate Charge (Qg) (Max) @ Vgs425nC @ 10VInput Capacitance (Ciss) (Max) @ Vds17000pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1170W (Tc)Rds On (Max) @ Id, Vgs33 mOhm @ 55A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227BPackage / CaseSOT-227-4, miniBLOC	Category	Discrete Semiconductor Products
Series HiPerFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 850V Current - Continuous Drain (Id) @ 25°C 110A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 425nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 17000pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) 1170W (Tc) Rds On (Max) @ Id, Vgs 33 mOhm @ 55A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227B Package / Case SOT-227-4, miniBLOC		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 850V Current - Continuous Drain (Id) @ 25°C 110A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 425nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 17000pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 1170W (Tc) Rds On (Max) @ Id, Vgs 33 mOhm @ 55A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227B Package / Case SOT-227B	Package	SOT-227-4, miniBLOC
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 110A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 850V 850V 850V 850V 110A (Tc) 110V 10V 10V 10V 110V 10V 1170W (Tc) 33 mOhm @ 55A, 10V 1170W (Tc) Chassis Mount SOT-227B SOT-227B	Series	HiPerFET?
Drain to Source Voltage (Vdss)850VCurrent - Continuous Drain (Id) @ 25°C110A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5.5V @ 8mAGate Charge (Qg) (Max) @ Vgs425nC @ 10VInput Capacitance (Ciss) (Max) @ Vds17000pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1170W (Tc)Rds On (Max) @ Id, Vgs33 mOhm @ 55A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227BPackage / CaseSOT-227-4, miniBLOC	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs 425nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 17000pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 33 mOhm @ 55A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Package / Case SOT-227-4, miniBLOC	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 5.5V @ 8mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 33 mOhm @ 55A, 10V Operating Temperature Chassis Mount Supplier Device Package Package / Case 10V 17000pF @ 25V ±30V 17000pF @ 25V 17000pF @ 25V	Drain to Source Voltage (Vdss)	850V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 17000pF @ 25V Vgs (Max) ### ### ############################	Current - Continuous Drain (Id) @ 25°C	110A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 17000pF @ 25V Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 33 mOhm @ 55A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package Package / Case SOT-227B SOT-227-4, miniBLOC	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 17000pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 33 mOhm @ 55A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227B Package / Case SOT-227-4, miniBLOC	Vgs(th) (Max) @ Id	5.5V @ 8mA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)1170W (Tc)Rds On (Max) @ Id, Vgs33 mOhm @ 55A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227BPackage / CaseSOT-227-4, miniBLOC	Gate Charge (Qg) (Max) @ Vgs	425nC @ 10V
FET Feature - Power Dissipation (Max) 1170W (Tc) Rds On (Max) @ Id, Vgs 33 mOhm @ 55A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227B Package / Case SOT-227-4, miniBLOC	Input Capacitance (Ciss) (Max) @ Vds	17000pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 33 mOhm @ 55A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227B Package / Case SOT-227-4, miniBLOC	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs33 mOhm @ 55A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeChassis MountSupplier Device PackageSOT-227BPackage / CaseSOT-227-4, miniBLOC	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Chassis Mount Supplier Device Package SOT-227B Package / Case SOT-227-4, miniBLOC	Power Dissipation (Max)	1170W (Tc)
Mounting TypeChassis MountSupplier Device PackageSOT-227BPackage / CaseSOT-227-4, miniBLOC	Rds On (Max) @ Id, Vgs	33 mOhm @ 55A, 10V
Supplier Device Package SOT-227B Package / Case SOT-227-4, miniBLOC	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case SOT-227-4, miniBLOC	Mounting Type	Chassis Mount
	Supplier Device Package	SOT-227B
Report errors?	Package / Case	SOT-227-4, miniBLOC
		Report errors?

IXFN110N85X Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXFN110N85X Payment Methods



















IXFN110N85X Shipping Methods













If you have any question about IXFN110N85X, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com